

## **Simultaneous imaging of upset and latchup-sensitive regions in a static RAM**

Fischer BE, Schlögl M, Barak J, Adler E, Metzger S

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Using the GSI heavy ion microprobe and a special hardware circuit for upset and latchup detection we have for the first time simultaneously imaged upset- and latchup-sensitive regions of a 2k x 8 bit static RAM (HM 65162) for different LET values of the beam and various operating voltages. Additionally we have mapped the scanned area by secondary electron imaging and ion induced charge imaging to create a data set as comprehensive as possible for the description of single event processes.